

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Wongsenakhum et al.

Attorney Docket No.:

Application No.: 10/815,560

NOVLP096/NVLS-2902

Examiner: Estrada, Michelle

Filed: March 31, 2004

Group: 2823

Title: METHOD OF FORMING LOW-

RESISTIVITY TUNGSTEN **INTERCONNECTS**

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail on February 15, 2006 in an envelope addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 2313-1450.

CERTIFICATE OF MAILING

Signed:

Tara Hayden

INFORMATION DISCLOSURE STATEMENT 37 CFR §§1.56 AND 1.97(b)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449, copies of which are attached, may be material to examination of the above-identified patent application. Applicants submit these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP096).

Respectfully submitted,

BEYER WEAVER & THOMAS, LLP

Denise S. Bergin

Registration No. 50,581

P.O. Box 70250 Oakland, CA 94612-0250

(Modified)

Information Disclosure Statement By Applicant Atty Docket No. NOVLP096/NVLS-2902 Application No.: 10/815,560

Applicant:

Wongsenakhum et al.

Filing Date

Group

(Use Several Sheets if Necessary)

March 31, 2004

2823

U.S. Patent Documents

U.S. Patent Documents							
Examiner		1				Sub-	Filing
Initial	No.	Patent No.	Date	Patentee	Class	class	Date
	A1	5,956,609	09.1999	Lee et al.			
	A2	2003/0104126	06.2003	Fang et al.			
					_		
	ļ					_	
					_	-	

Foreign Patent or Published Foreign Patent Application

Examiner		Document	Publication	Country or		Sub-	Trans	lation
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No

Other Documents

Examiner					
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication			
	C1	Chan et al., "Methods for Growing Low-Resistivity Tungsten Film", Novellus			
	1	Systems, Inc., filed November 1, 2005, Application No. 11/265,531, pages 1-35.			
		[NOVLP137/NVLS-0003093]			
	C2	Levy et al., "Deposition of Tungsten Nitride", Novellus Systems, Inc., filed			
		December 16, 2005, Application No. 11/305,368, pages 1-39.			
		[NOVLP063D1/NVLS-2615D1].			
	C3	U.S. Office Action mailed December 28, 2005, from U.S. Application No.			
		10/649,351 [NOVLP033X1/NVLS-000498X1].			
	1				
·					
Examiner	<u> </u>	Date Considered			

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.